



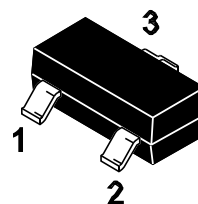
PJM10H03NSA

N-Channel Enhancement Mode Power MOSFET

Features

- High density cell design for ultra low $R_{DS(on)}$
- Excellent package for good heat dissipation
- $V_{DS} = 100V, I_D = 3A$
 $R_{DS(on)} < 160m\Omega @ V_{GS} = 10V$

SOT-23



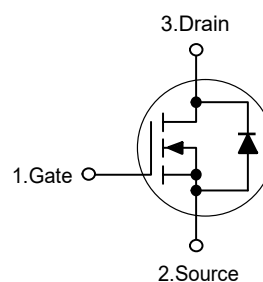
1. Gate 2. Source 3. Drain

Marking Code: 0103

Applications

- Power switching application
- Uninterruptible power supply

Schematic Diagram



Absolute Maximum Ratings

Ratings at 25°C ambient temperature unless otherwise specified.

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	3	A
Drain Current-Pulsed ^{Note1}	I_{DM}	30	A
Maximum Power Dissipation	P_D	0.9	W
Junction Temperature	T_J	150	°C
Storage Temperature Range	T_{STG}	-55 to +150	°C

Thermal Characteristics

Thermal Resistance, Junction-to-Ambient ^{Note2}	$R_{\theta JA}$	139	°C/W
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Electrical Characteristics

(Ta=25°C unless otherwise specified)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} =0V, I _D =250μA	100	--	--	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =100V, V _{GS} =0V	--	--	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	--	--	±100	nA
Gate Threshold Voltage ^{Note3}	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	1.0	1.6	2.0	V
Drain-Source On-Resistance ^{Note3}	R _{DS(on)}	V _{GS} =10V, I _D =3A	--	110	160	mΩ
		V _{GS} =4.5V, I _D =3A	--	150	170	mΩ
Forward Transconductance ^{Note3}	g _{FS}	V _{DS} =5V, I _D =1A	--	2.3	--	S
Dynamic Characteristics						
Input Capacitance	C _{iss}	V _{DS} =50V, V _{GS} =0V, f=1MHz	--	650	--	pF
Output Capacitance	C _{oss}		--	24	--	pF
Reverse Transfer Capacitance	C _{rss}		--	20	--	pF
Switching Characteristics						
Turn-on Delay Time	t _{d(on)}	V _{DD} =50V, R _L =19Ω V _{GS} =10V, R _{GEN} =3Ω	--	6	--	nS
Turn-on Rise Time	t _r		--	4	--	nS
Turn-off Delay Time	t _{d(off)}		--	20	--	nS
Turn-off Fall Time	t _f		--	4	--	nS
Total Gate Charge	Q _g	V _{DS} =50V, I _D =3A, V _{GS} =10V	--	20	--	nC
Gate-Source Charge	Q _{gs}		--	2.1	--	nC
Gate-Drain Charge	Q _{gd}		--	3.3	--	nC
Source-Drain Diode Characteristics						
Diode Forward Voltage ^{Note3}	V _{SD}	V _{GS} =0V, I _S =3A	--	--	1.2	V
Diode Forward Current ^{Note2}	I _S		--	--	3	A

Note: 1. Repetitive Rating: Pulse width limited by maximum junction temperature.

2. Surface Mounted on FR4 Board, $t \leq 10$ sec.

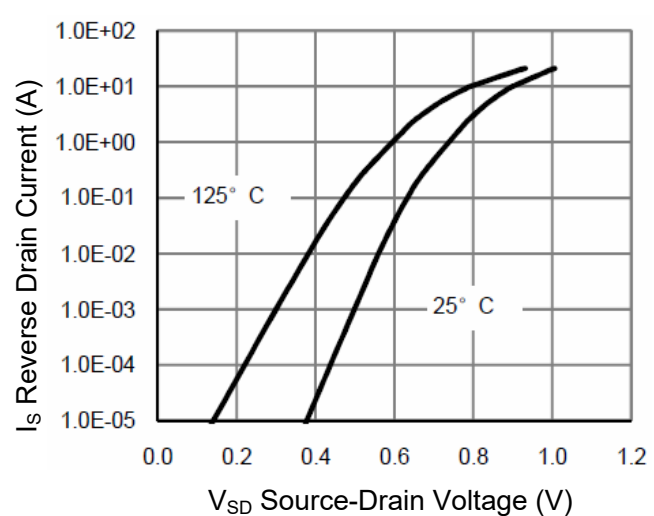
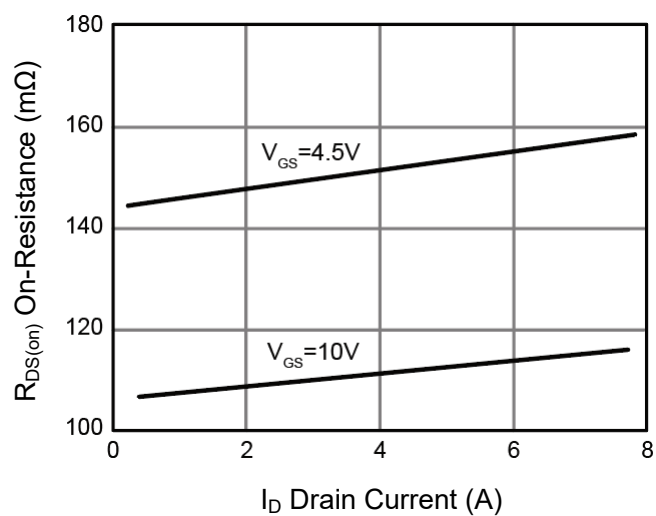
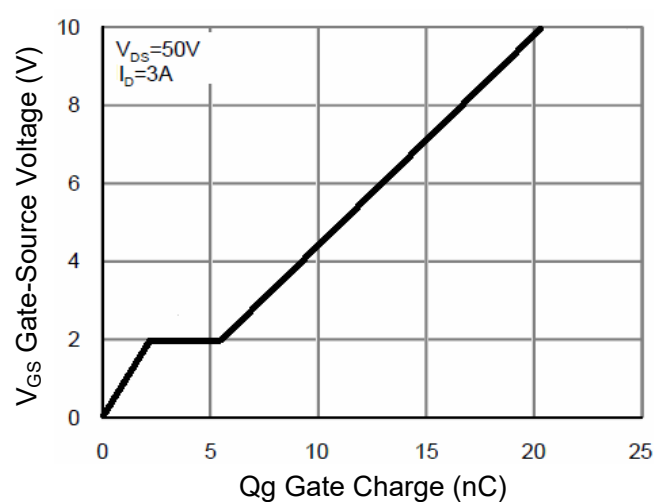
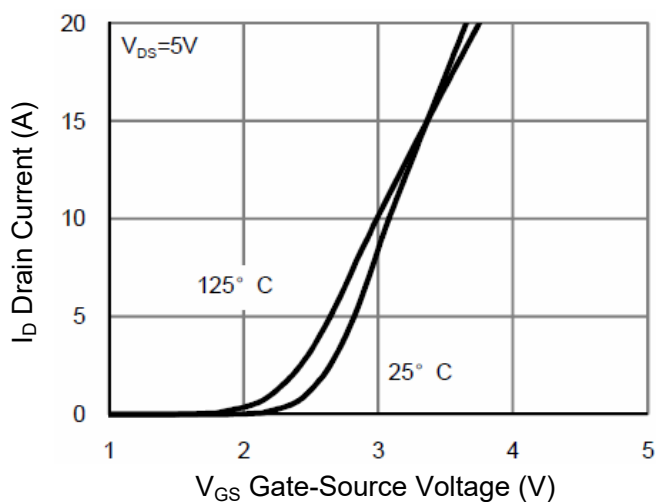
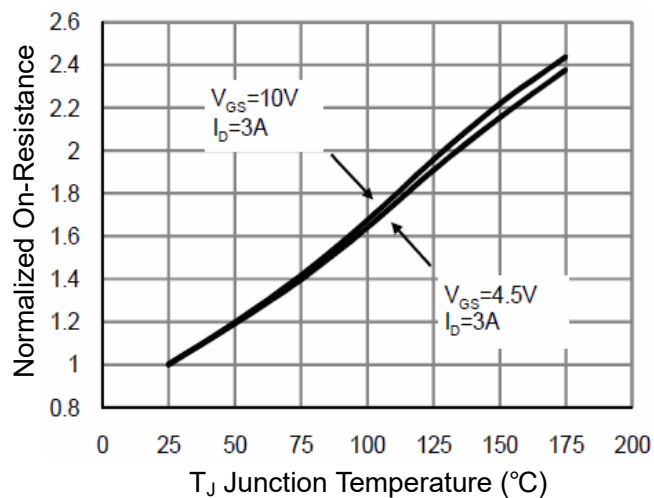
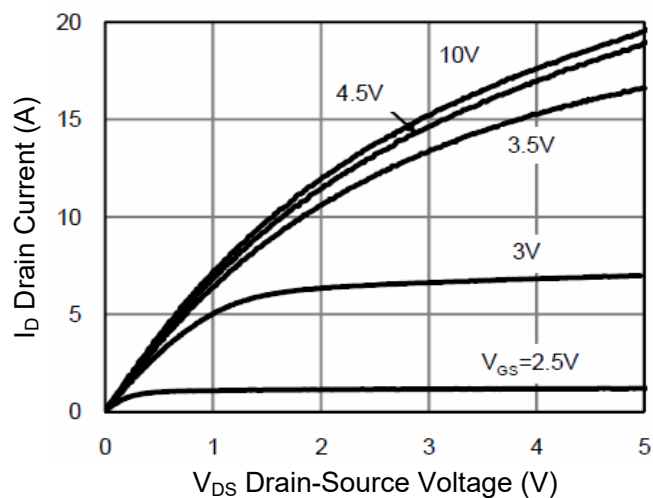
3. Pulse Test: Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.



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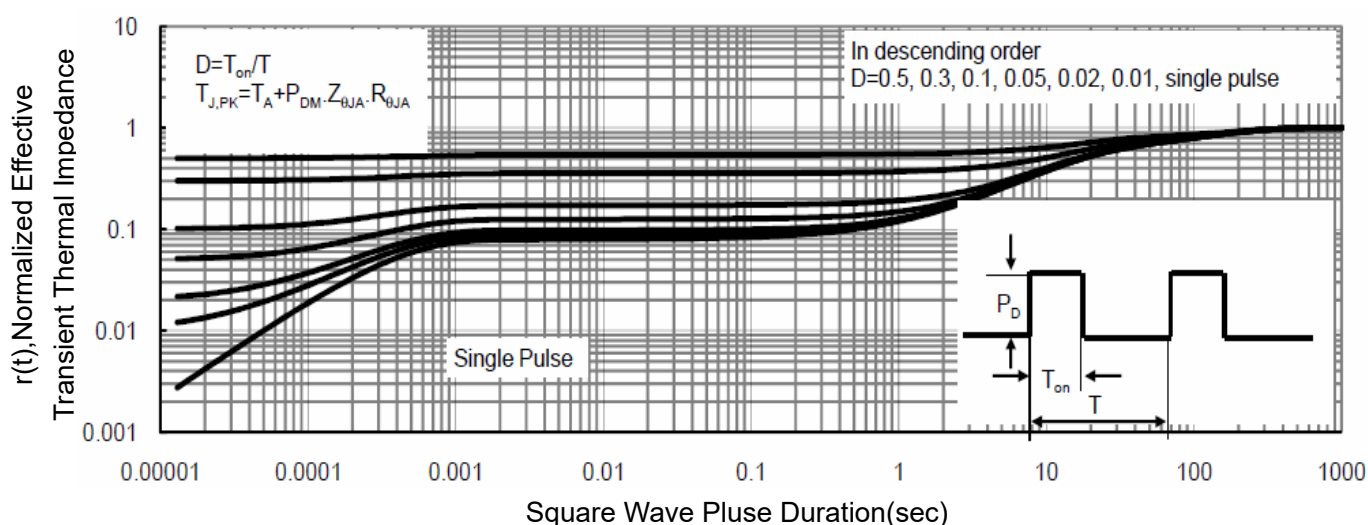
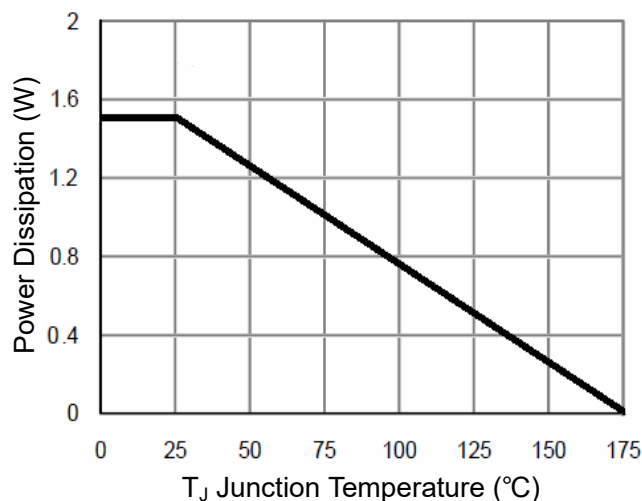
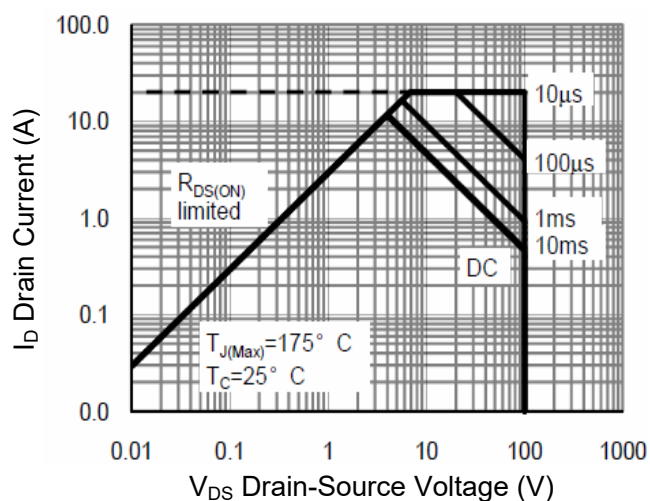
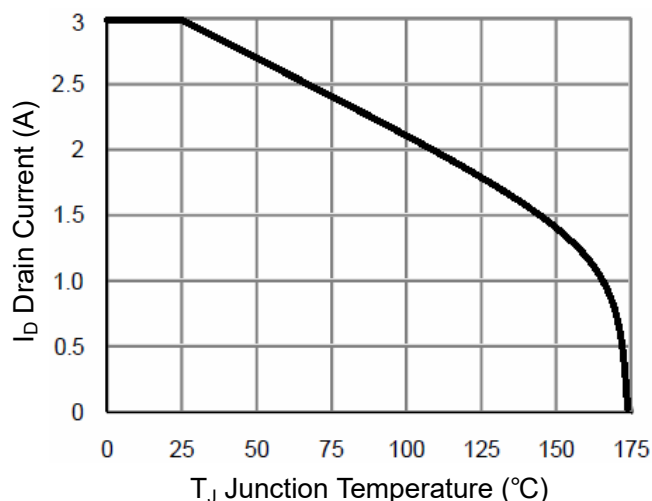
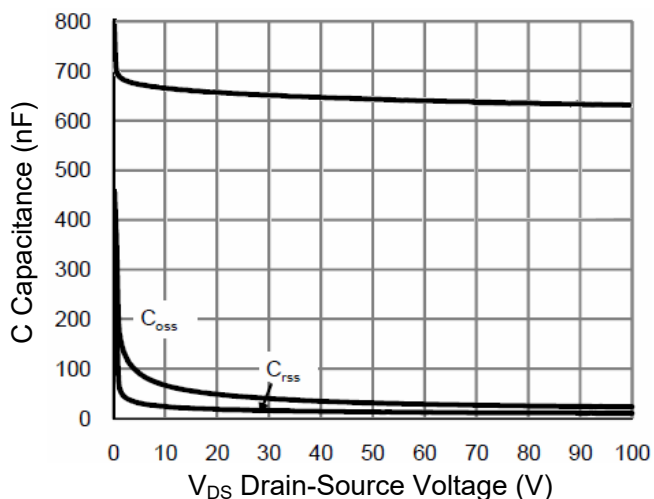
Typical Characteristic Curves





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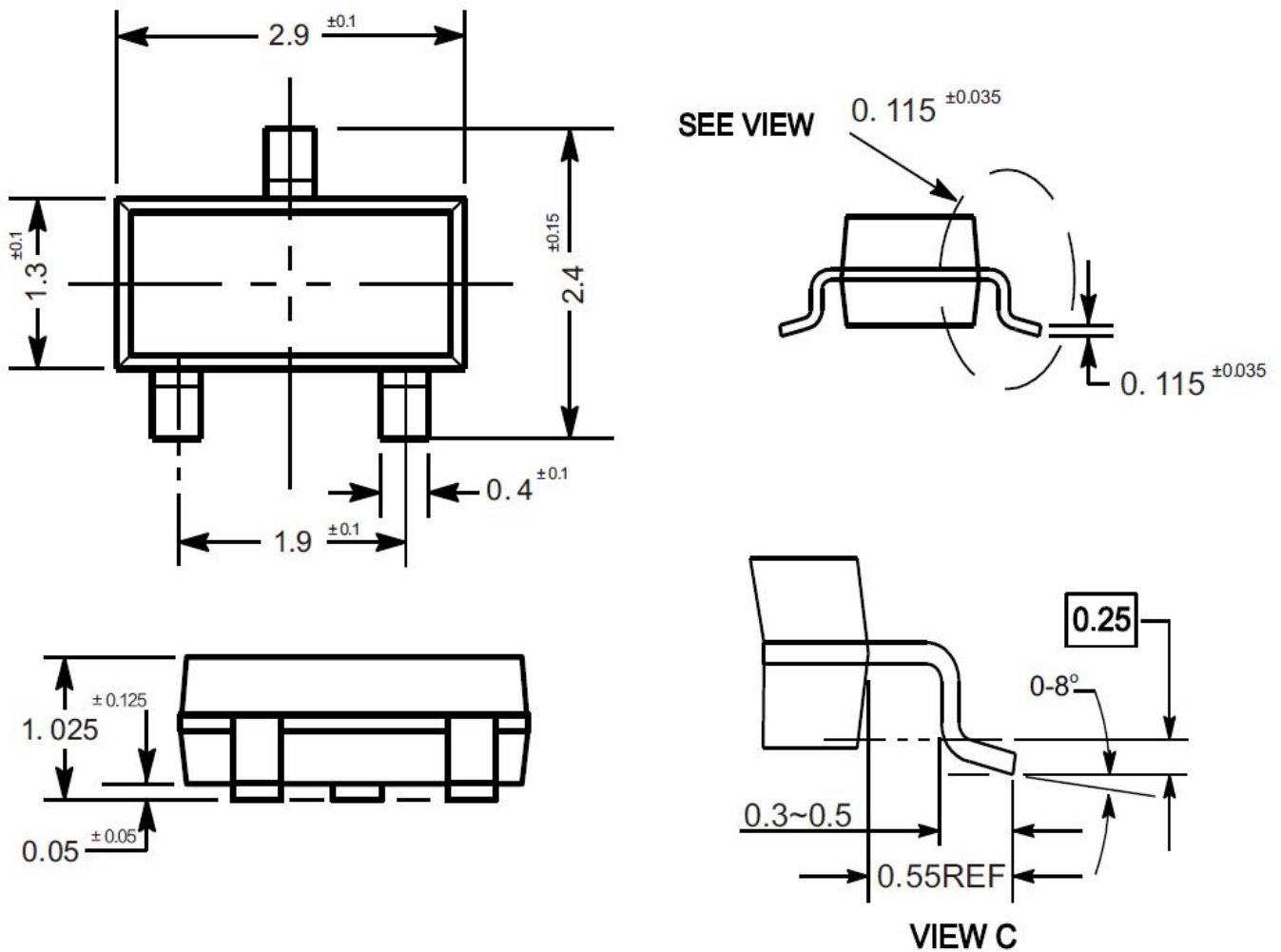
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Package Outline

SOT-23

Dimensions in mm



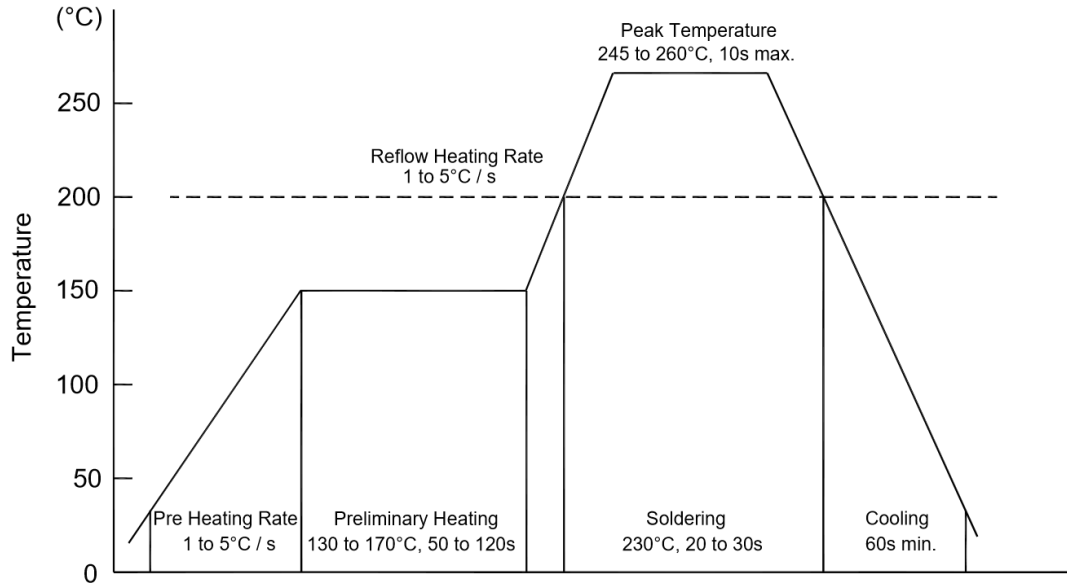
Ordering Information

Device	Package	Shipping
PJM10H03NSA	SOT-23	3,000PCS/Reel&7inches



Conditions of Soldering and Storage

◆ Recommended condition of reflow soldering



Recommended peak temperature is over 245 °C. If peak temperature is below 245 °C, you may adjust the following parameters:

- Time length of peak temperature (longer)
- Time length of soldering (longer)
- Thickness of solder paste (thicker)

◆ Conditions of hand soldering

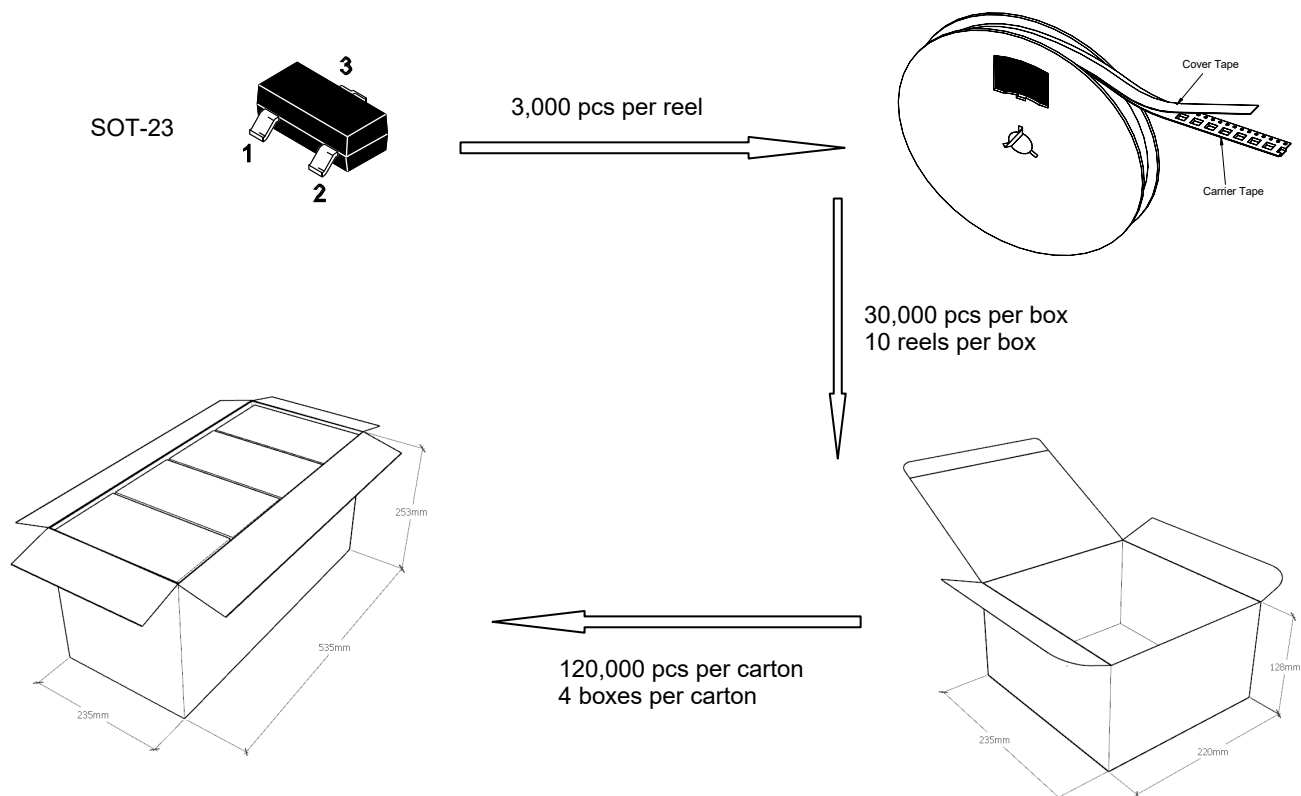
- Temperature: 370 °C
- Time: 3s max.
- Times: one time

◆ Storage conditions

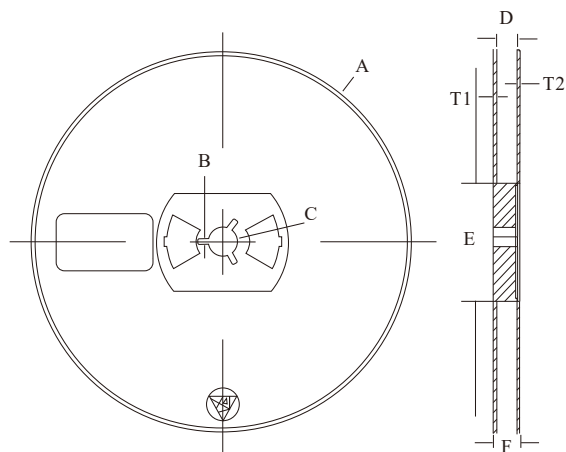
- **Temperature**
5 to 40 °C
- **Humidity**
30 to 80% RH
- **Recommended period**
One year after manufacturing

Package Specifications

- The method of packaging



◆ Embossed tape and reel data



Reel (7")

Symbol	Value (unit: mm)
A	$\varnothing 177.8 \pm 1$
B	2.7 ± 0.2
C	$\varnothing 13.5 \pm 0.2$
E	$\varnothing 54.5 \pm 0.2$
F	12.3 ± 0.3
D	$9.6 \pm 2 / -0.3$
T1	1.0 ± 0.2
T2	1.2 ± 0.2

